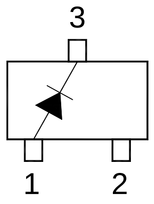
SB411D

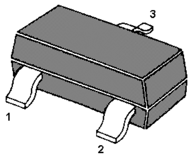
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for low power rectification and switching power supply

Features

- Small surface mounting type.
- High reliability.





SOT-23 Plastic Package

Marking

Marking Code: **FE**

Absolute Maximum Ratings (T_a = 25°C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	40	V
DC Reverse Voltage	V_R	20	V
Mean Rectifying Current	Io	0.5	A
Peak Forward Surge Current [1]	I_{FSM}	3	A
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-40 to +125	°C

[1] 60Hz for 1 ∿

Characteristics at T_a = 25 °C

Parameter	Symbol	Min	Typ	Max	Unit
Forward Voltage at I_F = 10mA at I_F = 500mA	V_F	- -	- -	0.3 0.5	V
Reverse Current at V_R =10V	I_R	-	-	30	µA
Capacitance Between Terminals at V_R =10V, f=1MHz	C_T	-	20	-	pF

●Electrical characteristic curves (Ta = 25°C)

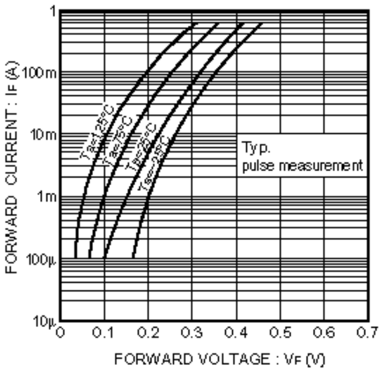


Fig. 1 Forward characteristics

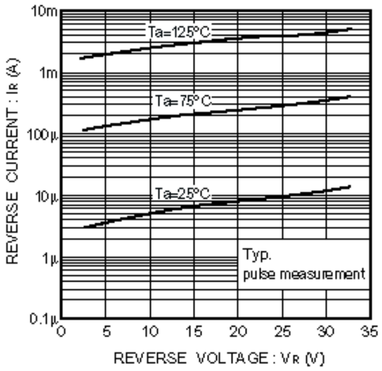


Fig. 2 Reverse characteristics

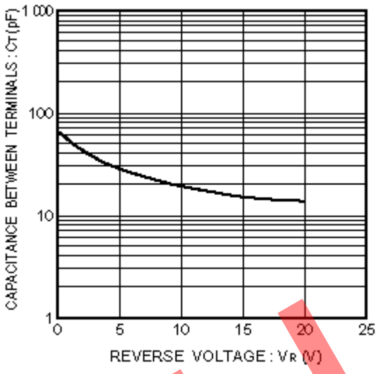


Fig. 3 Capacitance between terminals characteristic